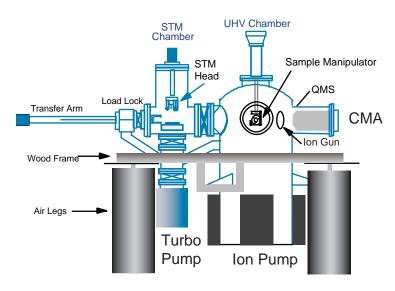
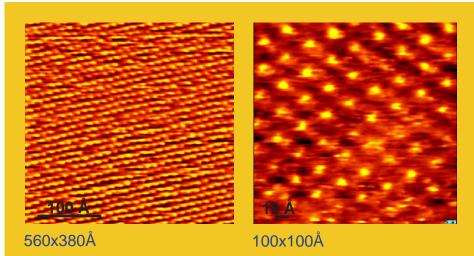


High Pressure, High Temperature Scanning Tunneling Microscope Developed

Berkeley Lab Instrument Shows Promise for In-Situ Studies of Catalytic Surfaces under Reaction Conditions



Clean single crystal metal samples are prepared in the UHV chamber (right) and transferred to the STM chamber (left) for atomic-scale imaging. A gate valve separates the two chambers. Samples can be heated to 700 K and exposed to gas pressures up to 1.5 atmospheres in the STM chamber. The entire instrument rests on a cushion of air to reduce vibrations.



Low resolution (left) and high resolution (right) images of clean Pt (111) exposed to 150 Torr CO and 50 Torr Q. The pattern of bright spots with 12.6 Å period ("Moire pattern") appeared after the surface was annealed at 456 K. It is caused by the interference of a single layer of CO with a 3.6 Å period and the underlying structure of the Pt (111) surface, which has a 2.77 Å period.